

BUK7222-55A

N-channel TrenchMOS standard level FET Rev. 2 — 23 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	48	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	103	W
Static chara	Static characteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 10}}{\text{Figure 11}};$	-	-	44	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 10}}{\text{Figure 11}};$ see Figure 11	-	19	22	mΩ
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 48 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω ; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	160	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		_G (EA)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7222-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	-	34	Α
		T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	48	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see <u>Figure 3</u>	<u>[1]</u> _	193	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	103	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	48	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	193	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 48 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	160	mJ

^[1] Peak drain current is limited by chip, not package.

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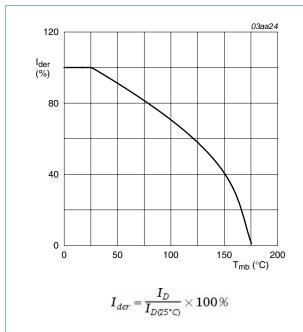


Fig 1. Normalized continuous drain current as a function of mounting base temperature

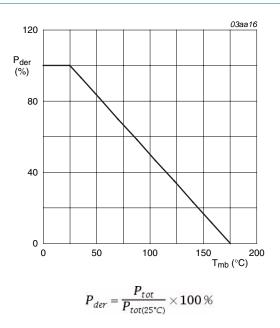
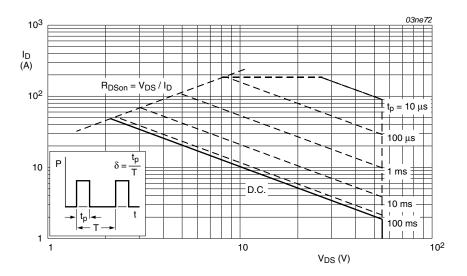


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	71.4	-	K/W

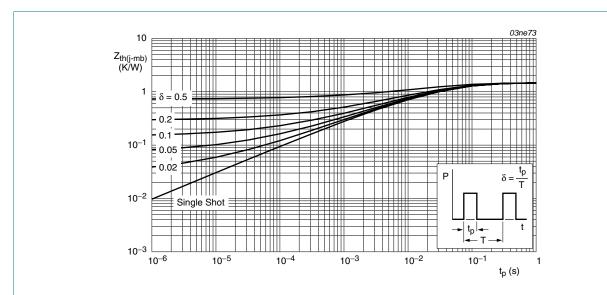


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 9	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 9	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 9	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon} drain-source or resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 10; see Figure 11	-	-	44	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 10; see Figure 11	-	19	22	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1200	1597	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	290	349	pF
C_{rss}	reverse transfer capacitance		-	180	245	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	74	-	ns
t _{d(off)}	turn-off delay time		-	70	-	ns
t _f	fall time		-	40	-	ns
L _D	internal drain inductance	measured from drain to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad; T _j = 25 °C	-	7.5	-	nΗ
		<u>'</u>				
Source-d	rain diode					
Source-d V _{SD}	rain diode source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	0.85	1.2	V
			-	0.85 45	1.2	V

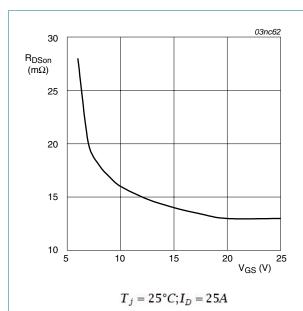


Fig 5. Drain-source on-state resistance as a function of drain current; typical values

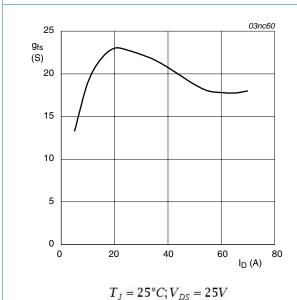
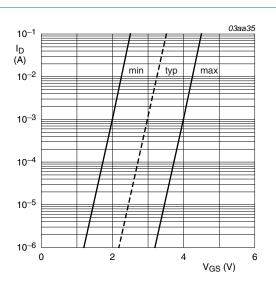
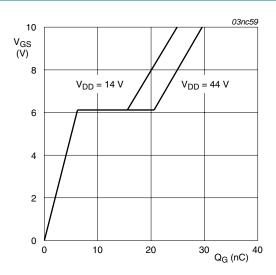


Fig 7. Forward transconductance as a function of drain current; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 6. Sub-threshold drain current as a function of gate-source voltage



 $T_j=25^{\circ}C; I_D=25A$

Fig 8. Gate-source voltage as a function of turn-on gate charge; typical values

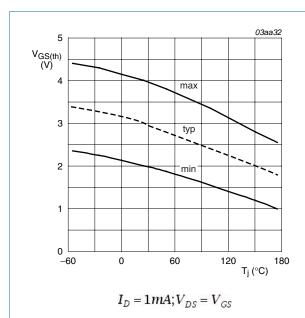


Fig 9. Gate-source threshold voltage as a function of junction temperature

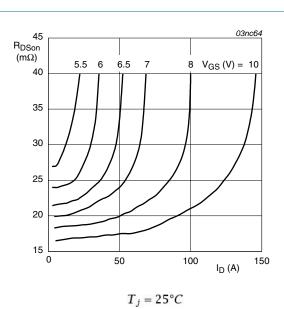


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

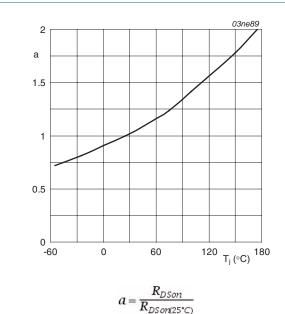
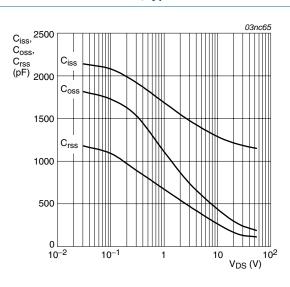


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



 $V_{GS} = 0V; f = 1MHz$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

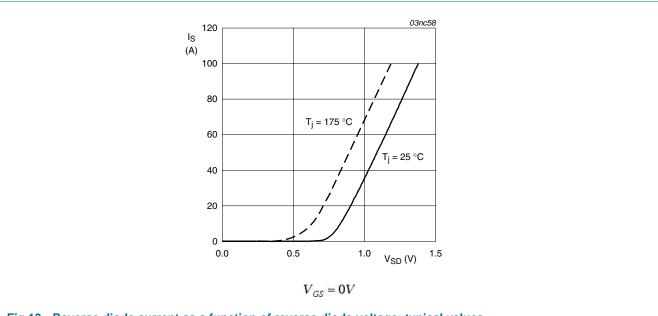


Fig 13. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

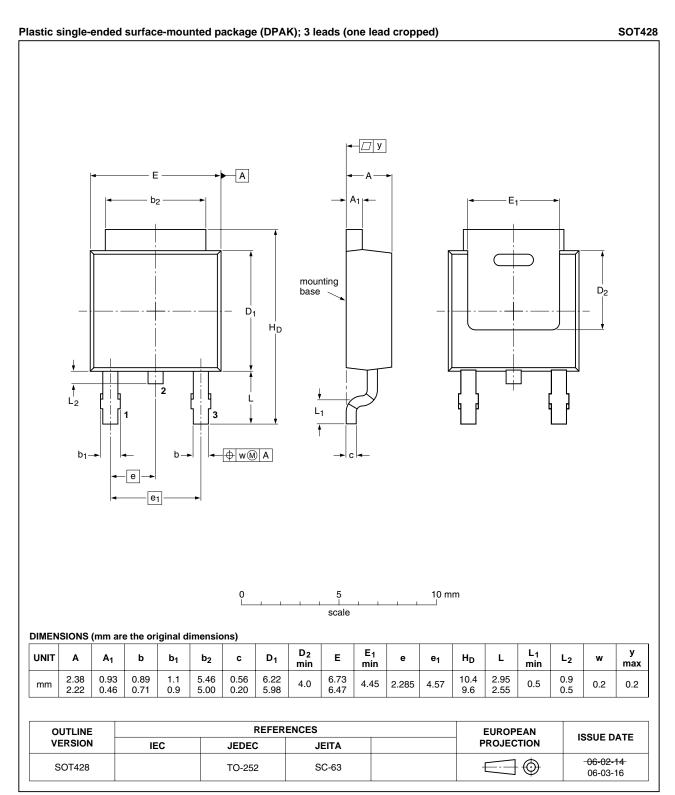


Fig 14. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK7222-55A v.2	20110223	Product data sheet	-	BUK7222_55A-01	
Modifications:		format of this data sheet has been redesigned to comply with the new identity guidelin KP Semiconductors.			
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.	
BUK7222_55A-01	20010417	Product specification	-	-	

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9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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ПОСТАВКА ЭЛЕКТРОННЫХ КОМПОНЕНТОВ

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